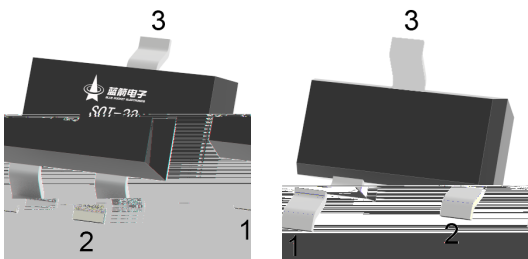
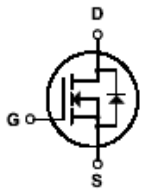


Rev.B Aug.-2023

SOT-23            N  
N- CHANNEL MOSFET in a SOT-23 Plastic Package.

$R_{DS(ON)}$             SOT-23  
Low  $R_{DS(ON)}$ ,SOT-23 package,HF Product.

DC-DC  
Battery management,High speed switch,low power DC to DC converter.



PIN1 G            PIN 2 S            PIN 3 D

Marking	A8H
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Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	20	V
Gate-Source Voltage		$V_{GSS}$	$\pm 10$	V
Drain Current – Continuous		$I_D$	4.5	A
Pulsed Drain Current		$I_{DM}$	12	A
Power Dissipation		$P_D$	1.4	W
Storage Temperature Range		$T_{stg}$	-55~150	
Maximum Junction-to-Ambient	$t \leq 10s$	$R_{JA}$	90	°C/W
Maximum Junction-to-Ambient	Steady-State		125	
Maximum Junction-to-Lead	Steady-State	$R_{JL}$	80	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0$ $I_D=250$ A	20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0$ $V_{DS}=20V$			1.0	A
Gate–Body Leakage.	$I_{GSS}$	$V_{GS}=\pm 10V$ $V_{DS}=0V$			$\pm 100$	nA
Static Drain–Source On–Resistance	$R_{DS(on)1}$	$V_{GS}=4.5V$ $I_D=4.5A$		21	25	m
	$R_{DS(on)2}$	$V_{GS}=2.5V$ $I_D=4.0A$		26	38	m
Forward Transconductance	$g_{FS}$	$V_{DS}=5V$ $I_D=4.5A$		6		S
Drain–Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ $I_D=1A$		0.74	1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=50$ A	0.5	0.6	1.0	V
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=10V,$ $f=1MHz$		500		pF
Output Capacitance	$C_{oss}$			255		
Reverse Transfer Capacitance	$C_{rss}$			210		
Gate resistance	$R_g$	$V_{GS}=V_{DS}=0V, f=1MHz$		1.7		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_g(10V)$	$V_{DS}=10V$ $V_{GS}=10V$ $I_D=4.5A$		12.5		nC
Total Gate Charge	$Q_g(4.5V)$			6		
Gate Source Charge	$Q_{gs}$			1		
Gate Drain Charge	$Q_{gd}$			2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=10V$ $V_{GS}=10V$ $R_{GEN}=3$ $R_L=1.7$		3		ns
Turn-On Rise Time	$t_r$			7.5		
Turn-Off Delay Time	$t_{d(off)}$			20		
Turn-Off Fall Time	$t_f$			6		

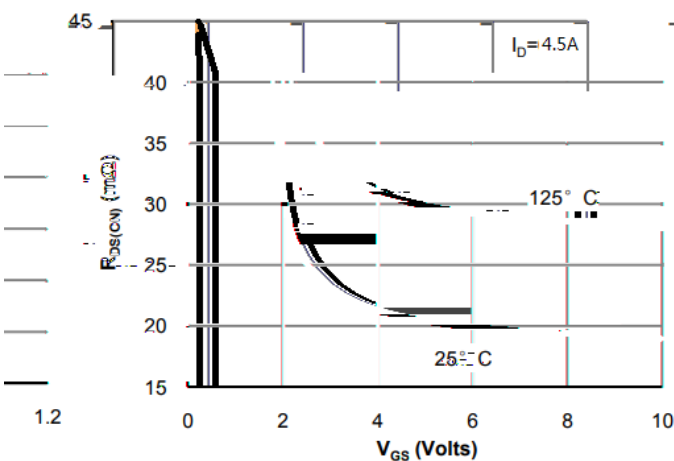
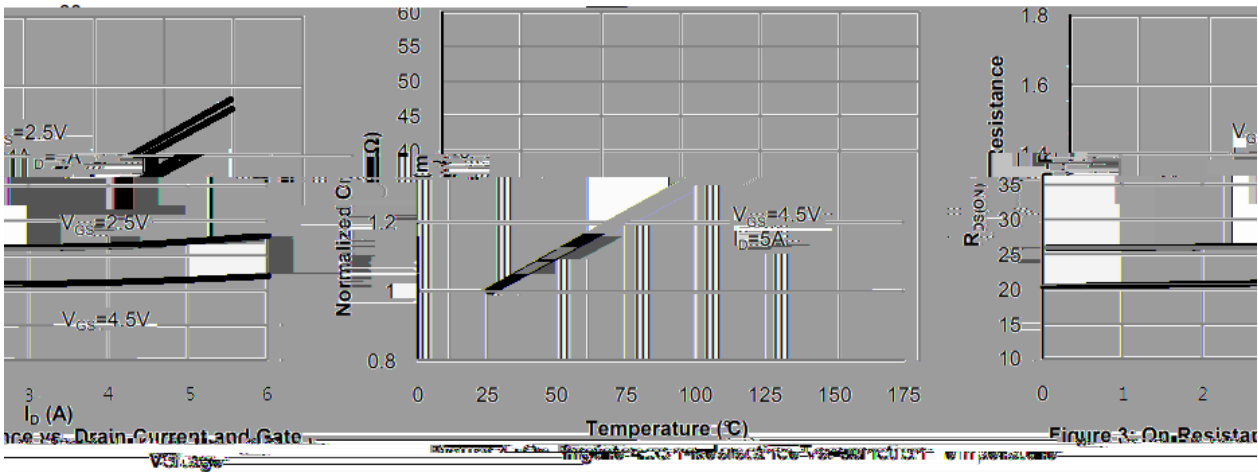
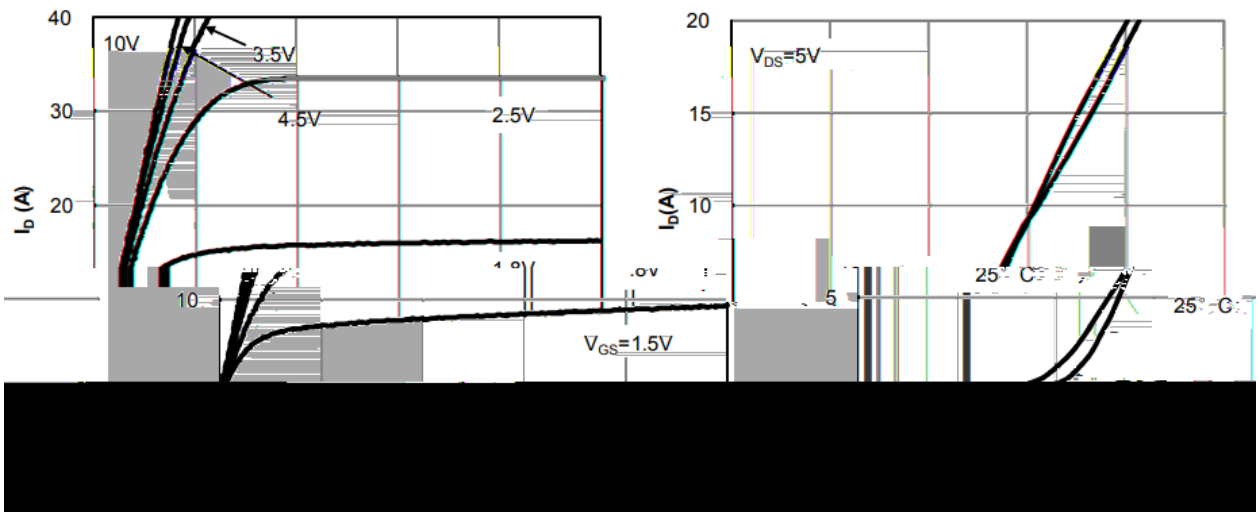


Figure 5: On-Resistance vs. Gate-Source Voltage

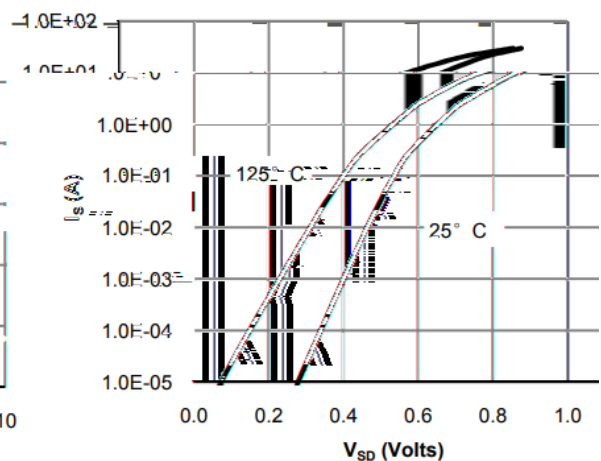
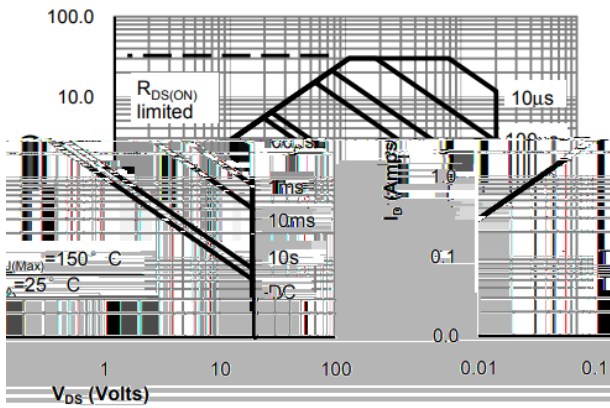
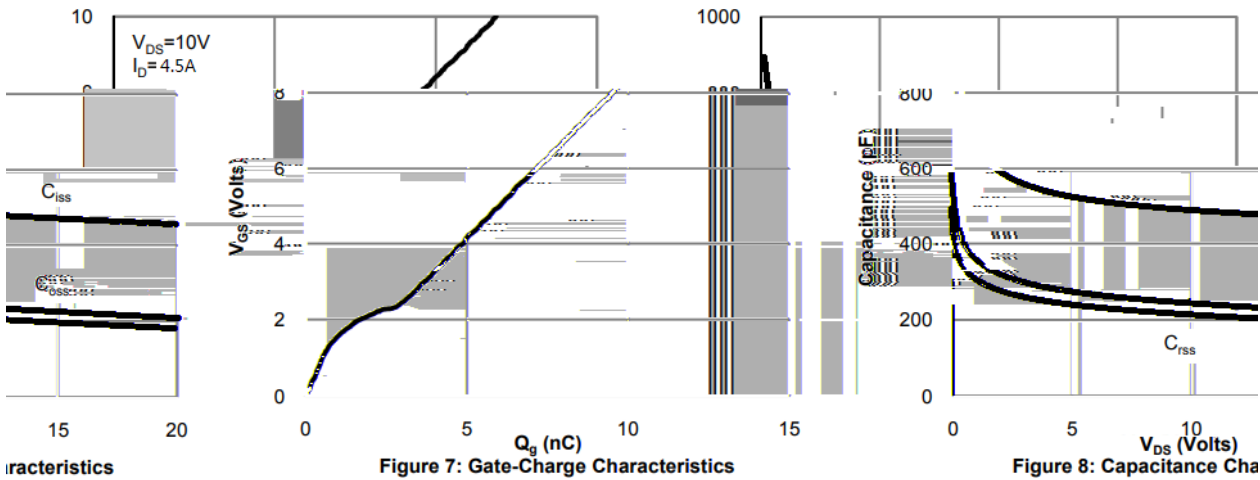
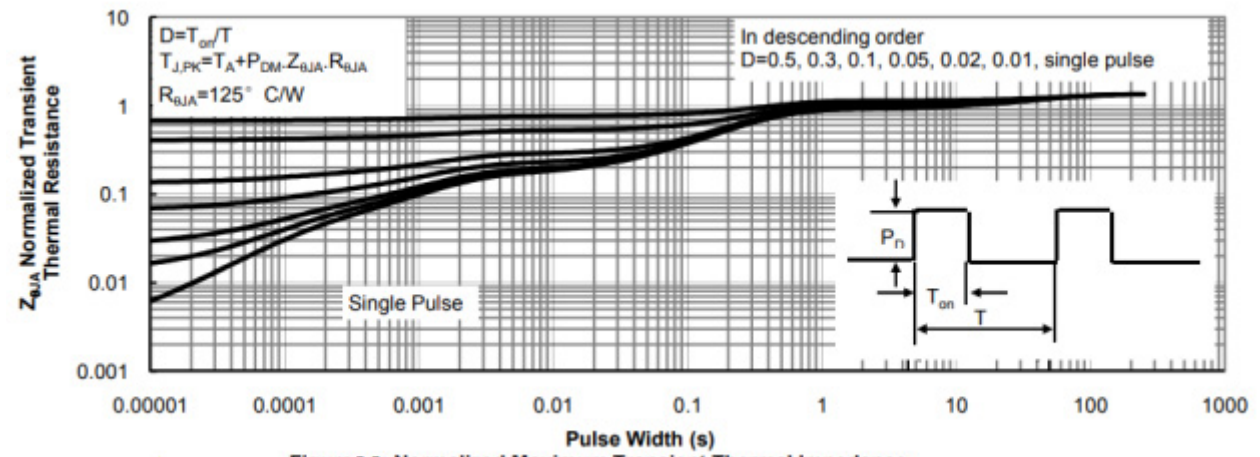


Figure 6: Body-Diode Characteristics

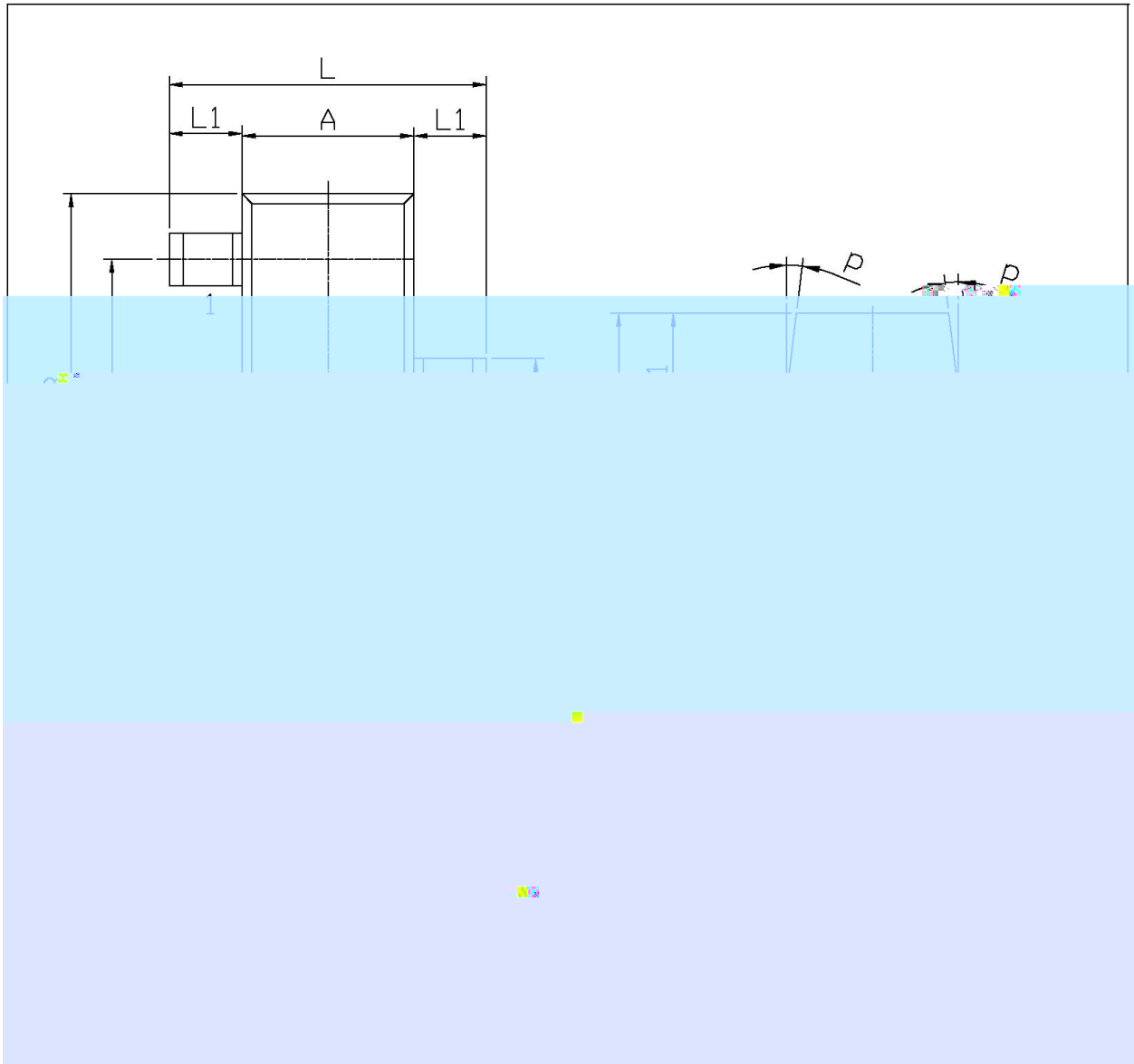


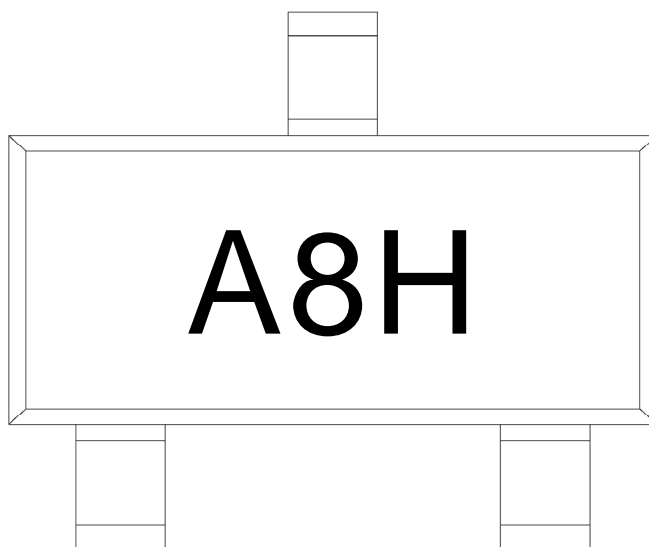
Maximum Forward Biased Safe Operating Area



SOT-23

单位: mm





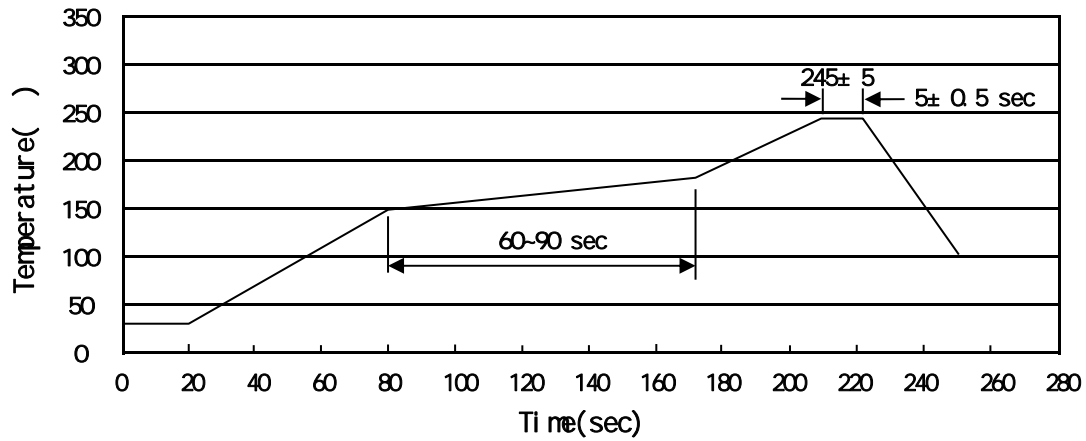
A8:

H:

Note:

A8      Product Type Code

H:      Company Code

**Temperature Profile for IR Reflow Soldering(Pb-Free)**


Note:

- |   |       |     |    |           |   |
|---|-------|-----|----|-----------|---|
| 1 | 150   | 180 | 60 | 90sec;    | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245±5 |     |    | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |       |     | 2  | 10 /sec.  | 3. Cooling Speed: 2~10 /sec.            |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm <sup>3</sup> )		
SOT-23	3,000	10	30,000	6	180,000	7" x8	180x120x180	390x385x205